

## High Voltage Diode

Device Type	Features	Page	VRRM	trr	Package
<a href="#">ESJA04-02A</a>	High Voltage Silicon Diode	7	2kV	0.08us max	
<a href="#">ESJA04-03A</a>	High Voltage Silicon Diode	7	3kV	0.08us max	
<a href="#">ESJA08-08</a>	HIGH VOLTAGE DIODE(8kV/5mA)	2	8kV max	0.05us max	Lead-11
<a href="#">ESJA09-10</a>	HIGH VOLTAGE DIODE(10kV/5mA)	2	10kV max	0.05us max	Lead-17
<a href="#">ESJA09-12</a>	HIGH VOLTAGE DIODE(12kV/5mA)	2	12kV max	0.05us max	Lead-17
<a href="#">ESJA28-02S</a>	HIGH VOLTAGE DIODE	2	2.2kV		
<a href="#">ESJA28-03</a>	HIGH VOLTAGE DIODE	2	2.7kV		
<a href="#">ESJA52-10A</a>	High Voltage Silicon Diode	7	10kV	0.08us max	
<a href="#">ESJA52-12A</a>	High Voltage Silicon Diode	7	12kV	0.08us max	
<a href="#">ESJA52-14A</a>	High Voltage Silicon Diode	7	14kV	0.08us max	
<a href="#">ESJA53-16A</a>	High Voltage Silicon Diode	7	16kV	0.08us max	
<a href="#">ESJA53-18A</a>	High Voltage Silicon Diode	7	18kV	0.08us max	
<a href="#">ESJA53-20A</a>	High Voltage Silicon Diode	7	20kV	0.08us max	
<a href="#">ESJA57-03A</a>	High Voltage Silicon Diode	7	3kV	0.08us max	
<a href="#">ESJA57-04A</a>	High Voltage Silicon Diode	7	4kV	0.08us max	
<a href="#">ESJA58-06A</a>	High Voltage Silicon Diode	7	6kV	0.08us max	
<a href="#">ESJA58-08A</a>	High Voltage Silicon Diode	7	8kV	0.08us max	

# SPECIFICATION

Device Name : High Voltage Silicon Diode

Type Name : ESJA57-04A

Spec. No. :

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Fuji Electric Co.,Ltd.  
Matsumoto Factory

	DATE	NAME	APPROVED	Fuji Electric Co.,Ltd.
DRAWN				DWG. NO.
CHECKED				

## 1. SCOPE

This specification provide the ratings and the requirements for high voltage silicon diode ESJA57-04A made by FUJI ELECTRIC CO.,LTD.

## 2. OUT VIEW

Shape and dimensions are described in Fig.3.

## 3. IDENTIFICATION

The diode shall be marked with Cathode Mark and Lot No..

## 4. RATINGS AND CHARACTERISTICS

### 4.1 ABSOLUTE MAX. RATINGS. ( Ta=25 °C unless otherwise noted. )

Items	Conditions	Symbols	Ratings	Units
Repetitive peak reverse voltage.		$V_{RRM}$	4	kVpeak
Non-Repetitive peak forward current.	50Hz Sine-half wave peak value	$I_{FSM}$	0.5	Apeak
Average forward current.	50Hz Sine Wave	$I_{AV}$	5	mA
Allowable junction temperature.		$T_j$	120	°C
Storage temperature range.		$T_{stg}$	-40~120	°C
Allowable operating case temperature.		$T_c$	100	°C

### 4.2 ELECTRICAL CHARACTERISTICS ( Ta=25 °C unless otherwise noted. )

Items	Conditions	Symbols	Ratings	Units
Maximum forward voltage drop	$I_F=10mA$	$V_F$	15	V
Maximum reverse current	$V_R=4kV$	$I_{R1}$	2	$\mu A$
Maximum reverse current	$V_R=4kV, 100^\circ C$	$I_{R2}$	5	$\mu A$
Maximum reverse recovery time	$I_F=2mA, I_R=4mA$	$t_{rr}$	0.08	$\mu S$
Maximum junction capacitance	$f=1MHz, V_R=0V$	$C_j$	2	pF

### 4.3 MECHANICAL CHARACTERISTICS

Weight : Ca. 0.2 gr.

Vibration proof : 5 G

Fuji Electric Co.,Ltd

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H04-004-03

Dimensions

Unit : mm

ESJA57-□□A

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